

Appl. No. 10/634,010  
Amdt. Dated 08/04/2004  
Reply to Office Action of May 10, 2004

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1-3. (Canceled)

4. (Currently Amended) The device of [claim 1] claim 30, wherein said reflector substantially reflects a laser energy used to laser trimming said thin film resistor.

5. (Currently Amended) The device of [claim 1] claim 30, wherein the thickness of said first dielectric layer is at a pre-determined thickness range which optimizes the laser trimming of said thin film resistor.

6. (Currently Amended) The device of [claim 1] claim 30, wherein said first dielectric layer comprises silicon dioxide ( $\text{SiO}_2$ ) and/or silicon nitride ( $\text{Si}_3\text{N}_4$ ).

7. (Currently Amended) The device of [claim 1] claim 30, wherein said thin film resistor comprises chromium silicon (CrSi), nickel chromium (NiCr), and/or tantalum nitride (TaN).

8. (Currently Amended) The device of [claim 1] claim 30, further comprising a second dielectric layer disposed over the thin film resistor.

9. (Original) The device of claim 8, wherein the thickness of said second dielectric layer is at a pre-determined thickness range which optimizes the laser trimming of said thin film resistor.

10. (Original) The device of claim 9, wherein said second dielectric layer comprises silicon dioxide ( $\text{SiO}_2$ ) and/or silicon nitride ( $\text{Si}_3\text{N}_4$ ).

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Claim 11. (Canceled)

12. (Currently Amended) The device of [claim 11] claim 31, wherein a plate of said MIM capacitor is [at a] the same layer as that of said reflector.

13. (Original) The device of claim 12, wherein said plate comprises an upper plate of said MIM capacitor.

Claims 14-15. (Canceled)

16. (Currently Amended) The method of [claim 15] claim 32, wherein said reflective layer comprises a refractory metal.

17. (Original) The method of claim 16, wherein said refractory metal comprises tungsten (W), molybdenum (Mo), tantalum (Ta), Rhenium (Re), and/or Niobium (Nb).

18. (Currently Amended) The method of [claim 14] claim 32, further comprising directing a laser energy to trim said thin film resistor, wherein said reflector substantially reflects said laser energy towards said thin film resistor.

19. (Original) The method of claim 18, wherein the thickness of said first dielectric layer is at a pre-determined thickness range which optimizes the laser trimming of said thin film resistor.

20. (Currently Amended) The method of [claim 14] claim 32, wherein said first dielectric layer comprises silicon dioxide ( $\text{SiO}_2$ ) and/or silicon nitride ( $\text{Si}_3\text{N}_4$ ).

Claim 21. (Canceled)

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22. (Currently Amended) The method of [claim 21] claim 33, wherein said thin film resistive layer comprises chromium silicon (CrSi), nickel chromium (NiCr), and/or tantalum nitride (TaN).

23. (Currently Amended) The method of [claim 14] claim 33, further comprising forming a second dielectric layer over said thin film resistor.

24. (Original) The method of claim 23, further comprising directing a laser energy to said thin film resistor, wherein the thickness of said second dielectric layer is at a predetermined range which optimizes the laser trimming of said thin film resistor.

25. (Original) The method of claim 23, wherein said second dielectric layer comprises silicon dioxide ( $\text{SiO}_2$ ) and/or silicon nitride ( $\text{Si}_3\text{N}_4$ ).

Claim 26. (Canceled)

27. (Currently Amended) The method of [claim 26] claim 34, wherein forming said MIM capacitor comprises:

forming a first capacitor plate;  
style="padding-left: 40px;">forming a second capacitor plate; and  
style="padding-left: 40px;">forming an insulating layer between said first and second capacitor plates.

28. (Original) The method of claim 27, wherein forming said second capacitor plate comprises:

forming an electrically-conductive layer;  
style="padding-left: 40px;">forming a mask layer over said electrically-conductive layer;  
style="padding-left: 40px;"> patterning and developing said mask layer to form first and second masks; and  
style="padding-left: 40px;">etching said electrically-conductive layer except first and second portions thereof which respectively underlie said first and second masks, wherein said first portion comprises said second capacitor plate and said second portion comprises said reflector.

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29. (Original) The method of claim 28, wherein said second capacitor plate comprises an upper capacitor plate of said MIM capacitor.

30. (New) A device comprising:  
a refractory metal reflector; the refractory metal comprising tungsten (W), molybdenum (Mo), tantalum (Ta), Rhenium (Re), and/or Niobium (Nb).,  
a first dielectric layer disposed over the reflector; and  
a thin film resistor formed over the first dielectric layer.

31. (New) A device comprising:  
a reflector;  
a first dielectric layer disposed over the reflector;  
a thin film resistor formed over the first dielectric layer, and  
a metal-insulator-metal (MIM) capacitor.

32. (New) A method comprising:  
forming a reflector comprising:  
forming a reflective layer;  
forming a mask layer over said reflective layer;  
patterning and developing said mask layer to form a mask; and  
etching said reflective layer except a portion underlying said mask, wherein said portion of said reflective layer comprises said reflector,  
forming a first dielectric layer over said reflector; and  
forming a thin film resistor over said first dielectric layer..

33. (New) A method comprising:  
forming a reflector;  
forming a first dielectric layer over said reflector; and  
forming a thin film resistor over said first dielectric layer comprising  
forming a thin film resistive layer over said first dielectric layer;  
forming a mask layer over said thin film resistive layer;

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patterning and developing said mask layer to form a mask; and  
etching said thin film resistive layer except a portion under said mask, wherein  
said portion comprises said thin film resistor.

34. (New) A method comprising:  
forming a reflector;  
forming a first dielectric layer over said reflector;  
forming a thin film resistor over said first dielectric layer, and  
forming a metal-insulator-metal (MIM) capacitor.